

RSS050P03

Transistors

Switching (-30V, -5.0A)

RSS050P03

●Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

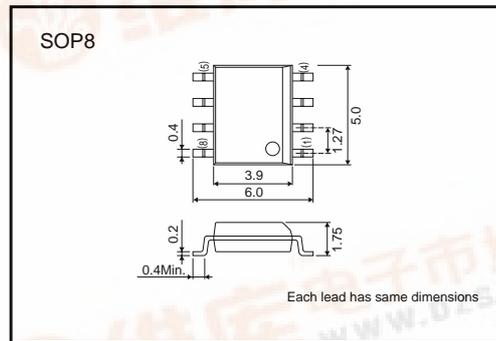
●Application

Power switching, DC / DC converter.

●Structure

Silicon P-channel
MOS FET

●External dimensions (Unit : mm)



●Packaging specifications

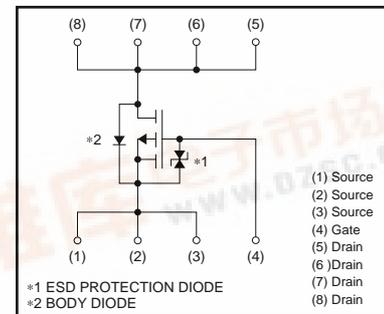
Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS050P03		○

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DS}	-30	V
Gate-source voltage	V _{GS}	±20	V
Drain current	Continuous	I _D ±5.0	A
	Pulsed	I _{DP} ±20	A *1
Source current (Body diode)	Continuous	I _S -1.6	A
	Pulsed	I _{SP} -20	A *1
Total power dissipation	P _D	2.0	W *2
Channel temperature	T _{ch}	150	°C
Range of Storage temperature	T _{stg}	-55 to +150	°C

*1 P_w≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board

●Equivalent circuit



●Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th (ch-a)}	62.5	°C / W *

* Mounted on a ceramic board.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	–30	–	–	V	I _D = –1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	–1	μA	V _{DS} = –30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	–1.0	–	–2.5	V	V _{DS} = –10V, I _D = –1mA
Static drain-source on-state resistance	R _{DS (on)} *	–	30	42	mΩ	I _D = –5.0A, V _{GS} = –10V
		–	47	65	mΩ	I _D = –2.5A, V _{GS} = –4.5V
		–	55	77	mΩ	I _D = –2.5A, V _{GS} = –4.0V
Forward transfer admittance	Y _{fs} *	5.0	–	–	S	V _{DS} = –10V, I _D = –2.5A
Input capacitance	C _{iss}	–	1200	–	pF	V _{DS} = –10V
Output capacitance	C _{oss}	–	250	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	180	–	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	–	12	–	ns	I _D = –2.5A
Rise time	t _r *	–	25	–	ns	V _{DD} ≐ –15V V _{GS} = –10V
Turn-off delay time	t _{d (off)} *	–	70	–	ns	R _L =6Ω
Fall time	t _f *	–	35	–	ns	R _{GS} =10Ω
Total gate charge	Q _g	–	13	–	nC	V _{DD} ≐ –15V
Gate-source charge	Q _{gs}	–	2.8	–	nC	V _{GS} = –5V
Gate-drain charge	Q _{gd}	–	5.0	–	nC	I _D = –5.0A

*Pulsed

Body diode characteristics (source-drain characteristics)

Forward voltage	V _{SD}	–	–	–1.2	V	I _S = –1.6A, V _{GS} =0V
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Transistors

●Electrical characteristic curves

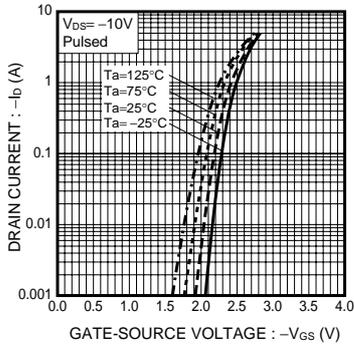


Fig.1 Typical Transfer Characteristics

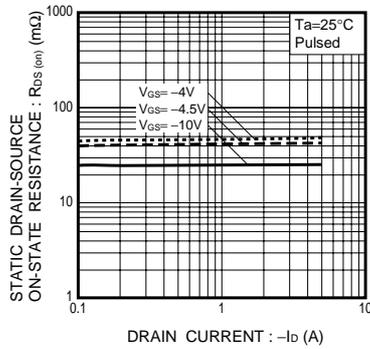


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

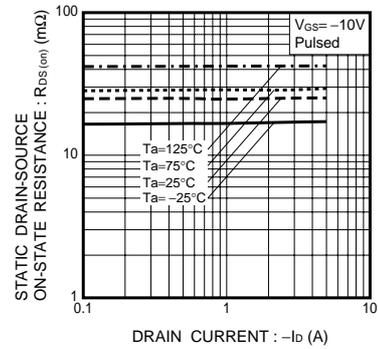


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

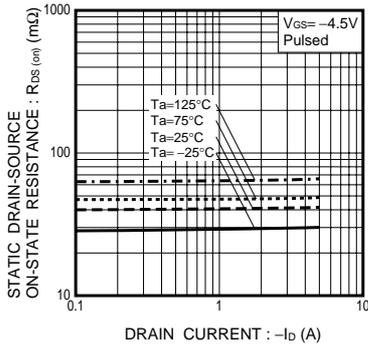


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

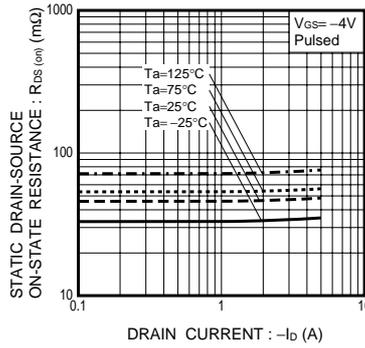


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

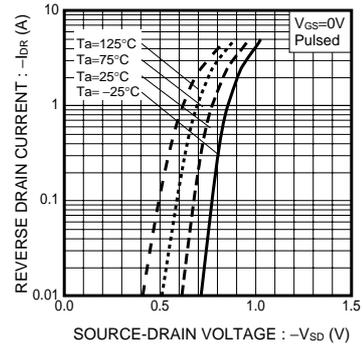


Fig.6 Reverse Drain Current Source-Drain Current

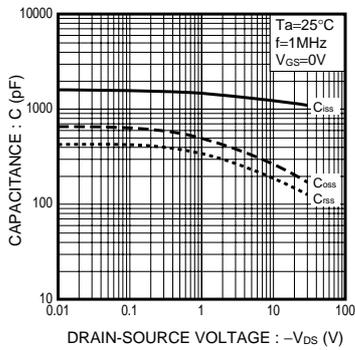


Fig.7 Typical Capacitance vs. Drain-Source Voltage

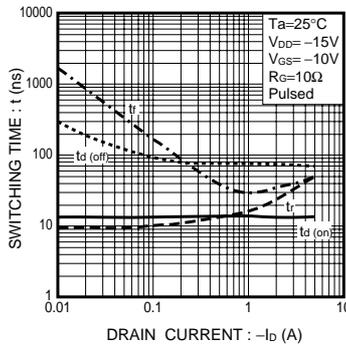


Fig.8 Switching Characteristics

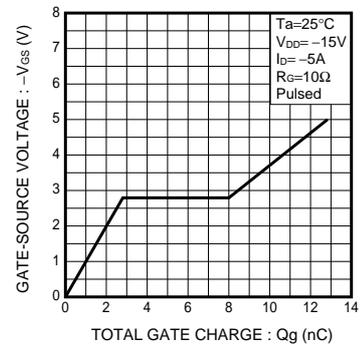


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

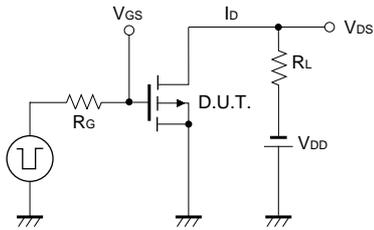


Fig.10 Switching Time Test Circuit

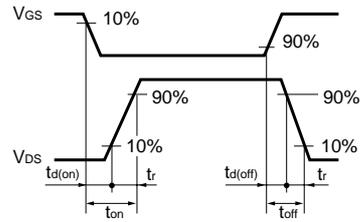


Fig.11 Switching Time Waveforms

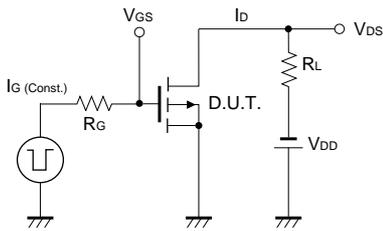


Fig.12 Gate Charge Test Circuit

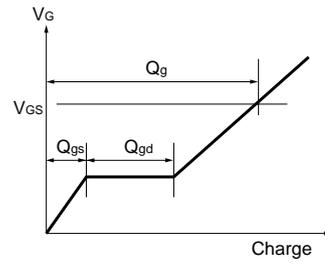


Fig.13 Gate Charge Waveform

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